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SCDS193D-AUGUST 2006-REVISED MARCH 2009

## **SPST CMOS ANALOG SWITCHES**

#### **FEATURES**

• 2-V to 12-V Single-Supply Operation

**JMENTS** 

- Specified ON-State Resistance:
  - 15 Ω Max With 12-V Supply
  - 20 Ω Max With 5-V Supply
  - 50 Ω Max With 3.3-V Supply
- Specified Low OFF-Leakage Currents:
  - 1 nA at 25°C
  - 10 nA at 85°C

- Specified Low ON-Leakage Currents:
  - 1 nA at 25°C
  - 10 nA at 85°C
- Low Charge Injection: 11.5 pC (12-V Supply)
- Fast Switching Speed:
  - $t_{ON} = 80 \text{ ns}, t_{OFF} = 50 \text{ ns} (12-V \text{ Supply})$
- Break-Before-Make Operation (t<sub>ON</sub> > t<sub>OFF</sub>)
- TTL/CMOS-Logic Compatible With 5-V Supply

### **DESCRIPTION/ORDERING INFORMATION**

The TS12A4514/TS12A4515 are single pole/single throw (SPST), low-voltage, single-supply CMOS analog switches, with very low switch ON-state resistance. The TS12A4514 is normally open (NO). The TS12A4515 is normally closed (NC).

These CMOS switches can operate continuously with a single supply between 2 V and 12 V. Each switch can handle rail-to-rail analog signals. The OFF-leakage current maximum is only 1 nA at 25°C or 10 nA at 85°C.

All digital inputs have 0.8-V to 2.4-V logic thresholds, ensuring TTL/CMOS-logic compatibility when using a 5-V supply.

For pin-compatible parts for use with dual supplies, see the TS12A4516/TS12A4517.

#### **ORDERING INFORMATION**

T <sub>A</sub>	PACKAG	6E <sup>(1)(2)</sup>	ORDERABLE PART NUMBER	TOP-SIDE MARKING(3)	
	PDIP – P	Reel of 1000	TS12A4514P	TS12A4514P	
	SOIC - D	Reel of 1500	TS12A4514D	YD514	
	30IC - D	Reel of 2500	TS12A4514DR	10014	
	SOP (SOT-23) – DBV	Reel of 3000	TS12A4514DBVR	9CJ_	
–40°C to 85°C	PDIP – P	Reel of 1000	TS12A4515P	TS12A4515P	
	SOIC - D	Reel of 1500	TS12A4515D	VDE4E	
	30IC - D	Reel of 2500	TS12A4515DR	YD515	
	SOP (SOT-23) - DBV	Reel of 3000	TS12A4515DBVR	9CK_	

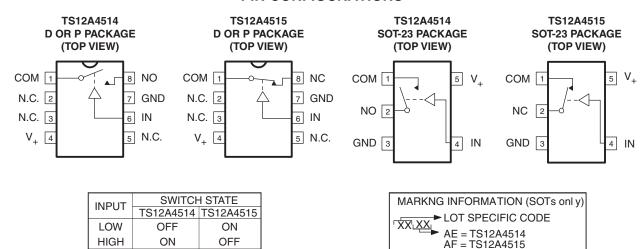
- (1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (3) DBV: The last character designates assembly/test Site



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#### PIN CONFIGURATIONS



N.C. - Not internally connected

NO - Normally open

NC - Normally closed

### **Absolute Minimum and Maximum Ratings**(1)(2)

voltages referenced to GND

			MIN	MAX	UNIT	
V <sub>+</sub>	Supply voltage range <sup>(3)</sup>	-0.3	13	V		
$V_{NC} V_{NO} V_{COM}$	Analog voltage range <sup>(4)</sup>	-0.3	V <sub>+</sub> + 0.3 or ±20 mA	V		
	Continuous current into any terminal				mA	
	Peak current, NO or COM (pulsed at 1 ms, 10% duty cycle)				mA	
	ESD per method 3015.7				V	
		8-pin plastic DIP (derate 9.09 mW/°C above 70°C)		727		
	Continuous power dissipation (T <sub>A</sub> = 70°C)	8-pin SOIC (derate 5.88 mW/°C above 70°C)		471	mW	
		5-pin SOT-23 (derate 7.1 mW/°C above 70°C)		571		
T <sub>A</sub>	Operating temperature range		-40	85	°C	
T <sub>stg</sub>	Storage temperature range		-65	150	°C	
	Lead temperature (soldering, 10 s)			300	°C	

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

<sup>(2)</sup> The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

<sup>(3)</sup> All voltages are with respect to ground, unless otherwise specified.

<sup>(4)</sup> Voltages exceeding V<sub>+</sub> or GND on any signal terminal are clamped by internal diodes. Limit forward-diode current to maximum current rating.

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# Electrical Characteristics for 5-V Supply<sup>(1)</sup>

 $V_{+} = 4.5 \text{ V}$  to 5.5 V,  $V_{INH} = 2.4 \text{ V}$ ,  $V_{INL} = 0.8 \text{ V}$ ,  $T_{A} = -40 ^{\circ}\text{C}$  to 85  $^{\circ}\text{C}$  (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T <sub>A</sub>	MIN TYP(2)	MAX	UNIT
Analog Switch		·	I	,		
Analog signal range	$V_{COM}, V_{NO}, V_{NC}$			0	V <sub>+</sub>	V
ON state resistance	_	$V_{+} = 4.5 \text{ V}, V_{COM} = 3.5 \text{ V},$	25°C	9.5	15	0
ON-state resistance	r <sub>on</sub>	I <sub>COM</sub> = 1 mA	Full		20	Ω
ON-state resistance	_	V <sub>COM</sub> = 1 V, 2 V, 3 V,	25°C	1	3	Ω
flatness	r <sub>on(flat)</sub>	I <sub>COM</sub> = 1 mA	Full		4	12
NO, NC	I <sub>NO(OFF)</sub> ,	V <sub>+</sub> = 5.5 V, V <sub>COM</sub> = 1 V,	25°C		1	nA
OFF leakage current (3)	I <sub>NC(OFF)</sub>	$V_{NO}$ or $V_{NC} = 4.5 \text{ V}$	Full		10	ΠA
СОМ	1	V <sub>+</sub> = 5.5 V, V <sub>COM</sub> = 1 V,	25°C		1	~ ^
OFF leakage current (3)	I <sub>COM(OFF)</sub>	$V_{NO}$ or $V_{NC} = 4.5 \text{ V}$	Full		10	nA
СОМ		V <sub>+</sub> = 5.5 V, V <sub>COM</sub> = 4.5 V,	25°C		1	A
ON leakage current (3)	I <sub>COM(ON)</sub>	$V_{NO}$ or $V_{NC} = 4.5 \text{ V}$	Full		10	nA
Digital Control Input (IN)				<u>.</u>		
Input logic high	V <sub>IH</sub>		Full	2.4	V <sub>+</sub>	V
Input logic low	V <sub>IL</sub>		Full	0	0.8	V
Input leakage current	I <sub>IH</sub> , I <sub>IL</sub>	V <sub>IN</sub> = V <sub>+</sub> , 0 V	Full		0.01	μΑ
Dynamic		·	I	,		
Time on time	t <sub>ON</sub>	Firmer 0	25°C	32	100	
Turn-on time		see Figure 2	Full		125	ns
Time off time		Figure 0	25°C	25	50	
Turn-off time	t <sub>OFF</sub>	see Figure 2	Full		60	ns
Charge injection <sup>(4)</sup>	$Q_{C}$	$C_L = 1 \text{ nF}, V_{NO} = 0 \text{ V},$ $R_S = 0 \Omega, \text{ See Figure 1}$	25°C	-3		рС
NO, NC OFF capacitance	$C_{NO(OFF)}$ , $C_{NC(OFF)}$	f = 1 MHz, See Figure 4	25°C	7.5		pF
COM OFF capacitance	$C_{COM(OFF)}$	f = 1 MHz, See Figure 4	25°C	7.5		pF
COM ON capacitance	C <sub>COM(ON)</sub>	f = 1 MHz, See Figure 4	25°C	19		pF
Digital input capacitance	Cı	V <sub>IN</sub> = V <sub>+</sub> , 0 V	25°C	1.5		pF
Bandwidth	BW	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C	475		MHz
OFF isolation	O <sub>ISO</sub>	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C	-94		dB
Total harmonic distortion	THD	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C	0.08		%
Supply						
V gunnhu gurrant	1	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	25°C		0.05	
V <sub>+</sub> supply current	I <sub>+</sub>	$V_{IN} = 0 \text{ V or } V_+$	Full		0.1	μΑ

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

Typical values are at  $T_A = 25$ °C. Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are ensured by correlation at 25°C.

Specified by design, not production tested



# Electrical Characteristics for 12-V Supply<sup>(1)</sup>

 $V_{+}$  = 11.4 V to 12.6 V,  $V_{INH}$  = 5 V,  $V_{INL}$  = 0.8 V,  $T_{A}$  = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	$T_A$	MIN TYP <sup>(2)</sup>	MAX	UNIT
Analog Switch						
Analog signal range	$V_{COM}, V_{NO}, V_{NC}$			0	V <sub>+</sub>	V
ON state mediates as		$V_{+} = 11.4 \text{ V}, V_{COM} = 10 \text{ V},$	25°C	6.5	10	0
ON-state resistance	r <sub>on</sub>	I <sub>COM</sub> = 1 mA	Full		15	Ω
ON-state resistance		V <sub>+</sub> = 11.4 V,	25°C	1.5	3	
flatness	r <sub>on(flat)</sub>	$V_{COM} = 2 \text{ V}, 5 \text{ V}, 10 \text{ V},$ $I_{COM} = 1 \text{ mA}$	Full		4	Ω
NO, NC	I <sub>NO(OFF)</sub> ,	$V_{+} = 12.6 \text{ V}, V_{COM} = 1 \text{ V},$	25°C		1	nA
OFF leakage current (3)	I <sub>NC(OFF)</sub>	$V_{NO}$ or $V_{NC} = 10 \text{ V}$	Full		10	ПА
СОМ		V <sub>+</sub> = 12.6 V, V <sub>COM</sub> = 1 V,	25°C		1	^
OFF leakage current <sup>(3)</sup>	I <sub>COM(OFF)</sub>	$V_{NO}$ or $V_{NC} = 10 \text{ V}$	Full		10	nA
СОМ		$V_{+} = 12.6 \text{ V}, V_{COM} = 10 \text{ V},$	25°C		1	A
ON leakage current <sup>(3)</sup>	I <sub>COM(ON)</sub>	$V_{+} = 12.6 \text{ V}, V_{COM} = 10 \text{ V}, V_{NO} \text{ or } V_{NC} = 10 \text{ V}$	Full		10	nA
Digital Control Input (IN)						
Input logic high	V <sub>IH</sub>		Full	5	V <sub>+</sub>	V
Input logic low	V <sub>IL</sub>		Full	0	0.8	V
Input leakage current	I <sub>IH</sub> , I <sub>IL</sub>	$V_{IN} = V_+, 0 V$	Full		0.01	μΑ
Dynamic						•
	ton	See Figure 2	25°C	22	75	
Turn-on time			Full		80	ns
			25°C	20	45	
Turn-off time	t <sub>OFF</sub>	See Figure 2	Full		50	ns
Charge injection <sup>(4)</sup>	$Q_{C}$	$C_L = 1 \text{ nF}, V_{NO} = 0 \text{ V},$ $R_S = 0 \Omega$ , See Figure 1	25°C	-11.5		рС
NO, NC OFF capacitance	C <sub>NO(OFF)</sub> C <sub>NC(OFF)</sub>	f = 1 MHz, See Figure 4	25°C	7.5		pF
COM OFF capacitance	C <sub>COM(OFF)</sub>	f = 1 MHz, See Figure 4	25°C	7.5		pF
COM ON capacitance	C <sub>COM(ON)</sub>	f = 1 MHz, See Figure 4	25°C	21.5		pF
Digital input capacitance	C <sub>I</sub>	V <sub>IN</sub> = V <sub>+</sub> , 0 V	25°C	1.5		pF
Bandwidth	BW	$R_L = 50 \ \Omega, \ C_L = 15 \ pF, \ V_{NO} = 1 \ V_{RMS}, \ f = 100 \ kHz$	25°C	520		MHz
OFF isolation	O <sub>ISO</sub>	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C	-95		dB
Total harmonic distortion	THD	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C	0.07		%
Supply		<u> </u>				
M. aumaha auma at		V 0.V == V	25°C		0.05	A
V <sub>+</sub> supply current	I <sub>+</sub>	$V_{IN} = 0 \text{ V or } V_+$	Full		0.2	μΑ

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

 <sup>(2)</sup> Typical values are at T<sub>A</sub> = 25°C.
(3) Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are ensured by correlation at 25°C.

Specified by design, not production tested

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## Electrical Characteristics for 3-V Supply<sup>(1)</sup>

 $V_{+} = 3 \text{ V}$  to 3.6 V,  $T_{A} = -40^{\circ}\text{C}$  to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T <sub>A</sub>	MIN TYP <sup>(2)</sup>	MAX	UNIT
Analog Switch		· ·		•		
Analog signal range	$V_{COM}$ , $V_{NO}$ , $V_{NC}$			0	V <sub>+</sub>	V
ON state registeres	_	$V_{+} = 3 \text{ V}, V_{COM} = 1.5 \text{ V},$	25°C	18.5	40	0
ON-state resistance	r <sub>on</sub>	$I_{NO} = 1 \text{ mA},$	Full		50	Ω
ON-state resistance		V <sub>+</sub> = 3 V,	25°C	1	3	
flatness	r <sub>on(flat)</sub>	V <sub>COM</sub> = 1 V, 1.5 V, 2 V, I <sub>COM</sub> = 1 mA	Full		4	Ω
NO, NC	I <sub>NO(OFF)</sub> ,	$V_{+} = 3.6 \text{ V}, V_{COM} = 1 \text{ V},$	25°C		1	nA
OFF leakage current (3)	I <sub>NC(OFF)</sub>	$V_{NO}$ or $V_{NC} = 3 \text{ V}$	Full		10	ПА
COM	I <sub>COM(OFF)</sub>	$V_{+} = 3.6 \text{ V}, V_{COM} = 1 \text{ V},$	25°C		1	nA
OFF leakage current <sup>(3)</sup>	'COM(OFF)	$V_{NO}$ or $V_{NC} = 3 \text{ V}$	Full		10	117 \
COM	I <sub>COM(ON)</sub>	$V_{+} = 3.6 \text{ V}, V_{COM} = 3 \text{ V}, V_{NO} \text{ or } V_{NC} = 3 \text{ V}$	25°C		1	nA
ON leakage current <sup>(3)</sup>	·COM(ON)	$V_{NO}$ or $V_{NC} = 3 \text{ V}$	Full		10	.,,
Digital Control Input (IN)					1	
Input logic high	$V_{IH}$		Full	2.4	$V_{+}$	V
Input logic low	$V_{IL}$		Full	0	8.0	V
Input leakage current	$I_{IH},I_{IL}$	$V_{IN} = V_+, 0 V$	Full		0.01	μΑ
Dynamic						
Turn-on time <sup>(4)</sup>	t <sub>ON</sub>	See Figure 2	25°C	63	120	ns
Turr-or time		See Figure 2	Full		175	113
Turn-off time <sup>(4)</sup>	t	See Figure 2	25°C	33	80	ns
	t <sub>OFF</sub>	Occ Figure 2	Full		120	113
Charge injection <sup>(4)</sup>	$Q_{C}$	C <sub>L</sub> = 1 nF, See Figure 1	25°C	-1.5		рC
NO, NC OFF capacitance	$C_{NO(OFF)},\ C_{NC(OFF)}$	f = 1 MHz, See Figure 4	25°C	7.5		pF
COM OFF capacitance	C <sub>COM(OFF)</sub>	f = 1 MHz, See Figure 4	25°C	7.5		pF
COM ON capacitance	C <sub>COM(ON)</sub>	f = 1 MHz, See Figure 4	25°C	17		pF
Digital input capacitance	C <sub>I</sub>	V <sub>IN</sub> = V <sub>+</sub> , 0 V	25°C	1.5		pF
Bandwidth	BW	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C	460		MHz
OFF isolation	O <sub>ISO</sub>	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C	-94		dB
Total harmonic distortion	THD	$R_L = 50 \ \Omega, \ C_L = 15 \ pF, \ V_{NO} = 1 \ V_{RMS}, \ f = 100 \ kHz$	25°C	0.15		%
Supply		<u> </u>			'	
V cumply ourrest	1	\/ - 0 \/ or \/	25°C		0.03	^
V <sub>+</sub> supply current	I <sub>+</sub>	$V_{IN} = 0 \text{ V or } V_+$	Full		0.05	μΑ

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

Typical values are at  $T_A = 25$ °C. Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are ensured by correlation at 25°C.

Specified by design, not production tested



# PIN DESCRIPTION(1)

	PIN	I NO.					
TS12	TS12A4514		TS12A4515		DESCRIPTION		
D, P	SOT-23	D, P	, P SOT-23				
1	1	1	1	COM	Common		
2, 3, 5	_	2, 3, 5	-	N.C.	No connect (not internally connected)		
4	5	4	5	V <sub>+</sub>	Power supply		
6	4	6	4	IN	Digital control to connect COM to NO or NC		
7	3	7	3	GND	Digital ground		
8	2	_	_	NO	Normally open		
_	_	8	2	NC	Normally closed		

<sup>(1)</sup> NO, NC, and COM pins are identical and interchangeable. Any may be considered as an input or an output; signals pass in both directions.



#### **APPLICATION INFORMATION**

### **Power-Supply Considerations**

The TS12A4514/TS12A4515 construction is typical of most CMOS analog switches, except that they have only two supply pins:  $V_+$  and GND.  $V_+$  and GND drive the internal CMOS switches and set their analog voltage limits. Reverse ESD-protection diodes are internally connected between each analog-signal pin and both  $V_+$  and GND. One of these diodes conducts if any analog signal exceeds  $V_+$  or GND.

Virtually all the analog leakage current comes from the ESD diodes to  $V_+$  or GND. Although the ESD diodes on a given signal pin are identical and, therefore, fairly well balanced, they are reverse biased differently. Each is biased by either  $V_+$  or GND and the analog signal. This means their leakages will vary as the signal varies. The difference in the two diode leakages to the  $V_+$  and GND pins constitutes the analog-signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of the same or opposite polarity.

There is no connection between the analog-signal paths and  $V_{+}$  or GND.

 $V_+$  and GND also power the internal logic and logic-level translators. The logic-level translators convert the logic levels to switched  $V_+$  and GND signals to drive the analog signal gates.

### **Logic-Level Thresholds**

The logic-level thresholds are CMOS/TTL compatible when  $V_+$  is 5 V. As  $V_+$  is raised, the level threshold increases slightly. When  $V_+$  reaches 12 V, the level threshold is about 3 V – above the TTL-specified high-level minimum of 2.8 V, but still compatible with CMOS outputs.

#### **CAUTION:**

If the user is using the TS12A4514 or TS12A4515 with a V+ supply of 3 V, then the control input (IN) voltage should not exceed V+, otherwise the output levels can exceed 3 V and violate the absolute maximum rating, potentially damaging the device.

### **High-Frequency Performance**

In  $50-\Omega$  systems, signal response is reasonably flat up to 250 MHz (see *Typical Operating Characteristics*). Above 20 MHz, the on response has several minor peaks that are highly layout dependent. The problem is not in turning the switch on; it is turning it off. The OFF-state switch acts like a capacitor and passes higher frequencies with less attenuation. At 10 MHz, OFF isolation is about -45 dB in  $50-\Omega$  systems, decreasing (approximately 20 dB per decade) as frequency increases. Higher circuit impedances also make OFF isolation decrease. OFF isolation is about 3 dB above that of a bare IC socket, and is due entirely to capacitive coupling.

#### **Test Circuits/Timing Diagrams**

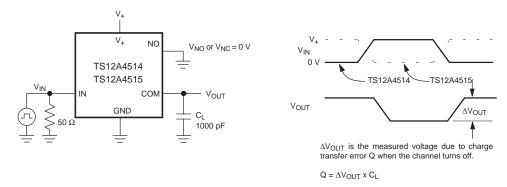


Figure 1. Charge Injection



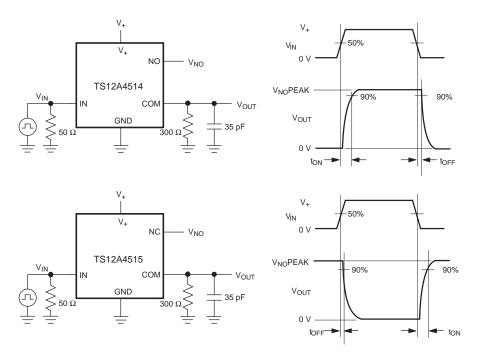


Figure 2. Switching Times

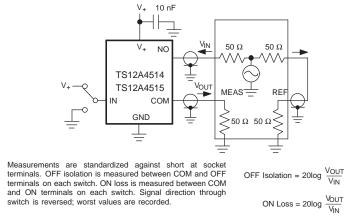


Figure 3. OFF Isolation and ON Loss

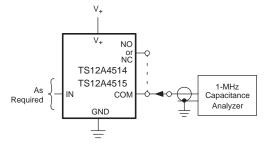


Figure 4. NO, NC, and COM Capacitance

#### PACKAGE OPTION ADDENDUM

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#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp (3)
TS12A4514D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4514DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4514DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4514DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4514DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4514P	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TS12A4514PE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TS12A4515D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4515DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4515DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4515DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4515DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS12A4515P	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TS12A4515PE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is



## **PACKAGE OPTION ADDENDUM**

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# PACKAGE MATERIALS INFORMATION

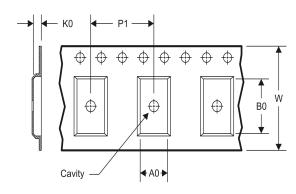
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### TAPE AND REEL INFORMATION

### **REEL DIMENSIONS**







A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### TAPE AND REEL INFORMATION

\*All dimensions are nominal

All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS12A4514DBVR	SOT-23	DBV	5	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TS12A4514DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TS12A4515DBVR	SOT-23	DBV	5	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TS12A4515DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

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\*All dimensions are nominal

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Device	Package Type	ackage Type Package Drawing Pi		SPQ	Length (mm)	Width (mm)	Height (mm)
TS12A4514DBVR	SOT-23	DBV	5	3000	203.0	203.0	35.0
TS12A4514DR	SOIC	D	8	2500	367.0	367.0	35.0
TS12A4515DBVR	SOT-23	DBV	5	3000	203.0	203.0	35.0
TS12A4515DR	SOIC	D	8	2500	367.0	367.0	35.0

# P (R-PDIP-T8)

## PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



# DBV (R-PDSO-G5)

# PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
  - D. Falls within JEDEC MO-178 Variation AA.



# DBV (R-PDSO-G5)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



# D (R-PDSO-G8)

### PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



# D (R-PDSO-G8)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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